

IS61LPS25632T/D

IS61LPS25636T/D

IS61LPS51218T/D



256K x 32, 256K x 36, 512K x 18 SYNCHRONOUS PIPELINED, SINGLE-CYCLE DESELECT STATIC RAM

DECEMBER 2003

FEATURES

- Internal self-timed write cycle
- Individual Byte Write Control and Global Write
- Clock controlled, registered address, data and control
- Linear burst sequence control using MODE input
- Three chip enable option for simple depth expansion and address pipelining
- Common data inputs and data outputs
- JEDEC 100-Pin TQFP package
- Power Supply
 - +3.3V V_{DD}
 - +3.3V or 2.5 V_{DDQ} (I/O)
- Auto Power-down during deselect
- Single cycle deselect
- Snooze MODE for reduced-power standby
- T Version (three chips selects)
- D Version (two chips selects)

DESCRIPTION

The *ISSI* IS61LPS25632T/D, IS61LPS25636T/D, and IS61LPS51218T/D are high-speed, low-power synchronous static RAMs designed to provide burstable, high-performance memory for communication and networking applications. The IS61LPS25632T/D is organized as 262,144 words by 32 bits and the IS61LPS25636T/D is organized as 262,144 words by 36 bits. The IS61LPS51218T/D is organized as 524,288 words by 18 bits. Fabricated with *ISSI*'s advanced CMOS technology, the device integrates a 2-bit burst counter, high-speed SRAM core, and high-drive capability outputs into a single monolithic circuit. All synchronous inputs pass through registers controlled by a positive-edge-triggered single clock input.

Write cycles are internally self-timed and are initiated by the rising edge of the clock input. Write cycles can be one to four bytes wide as controlled by the write control inputs.

Separate byte enables allow individual bytes to be written. Byte write operation is performed by using byte write enable ($\overline{\text{BWE}}$). Input combined with one or more individual byte write signals ($\overline{\text{BWx}}$). In addition, Global Write ($\overline{\text{GW}}$) is available for writing all bytes at one time, regardless of the byte write controls.

Bursts can be initiated with either $\overline{\text{ADSP}}$ (Address Status Processor) or $\overline{\text{ADSC}}$ (Address Status Cache Controller) input pins. Subsequent burst addresses can be generated internally and controlled by the $\overline{\text{ADV}}$ (burst address advance) input pin.

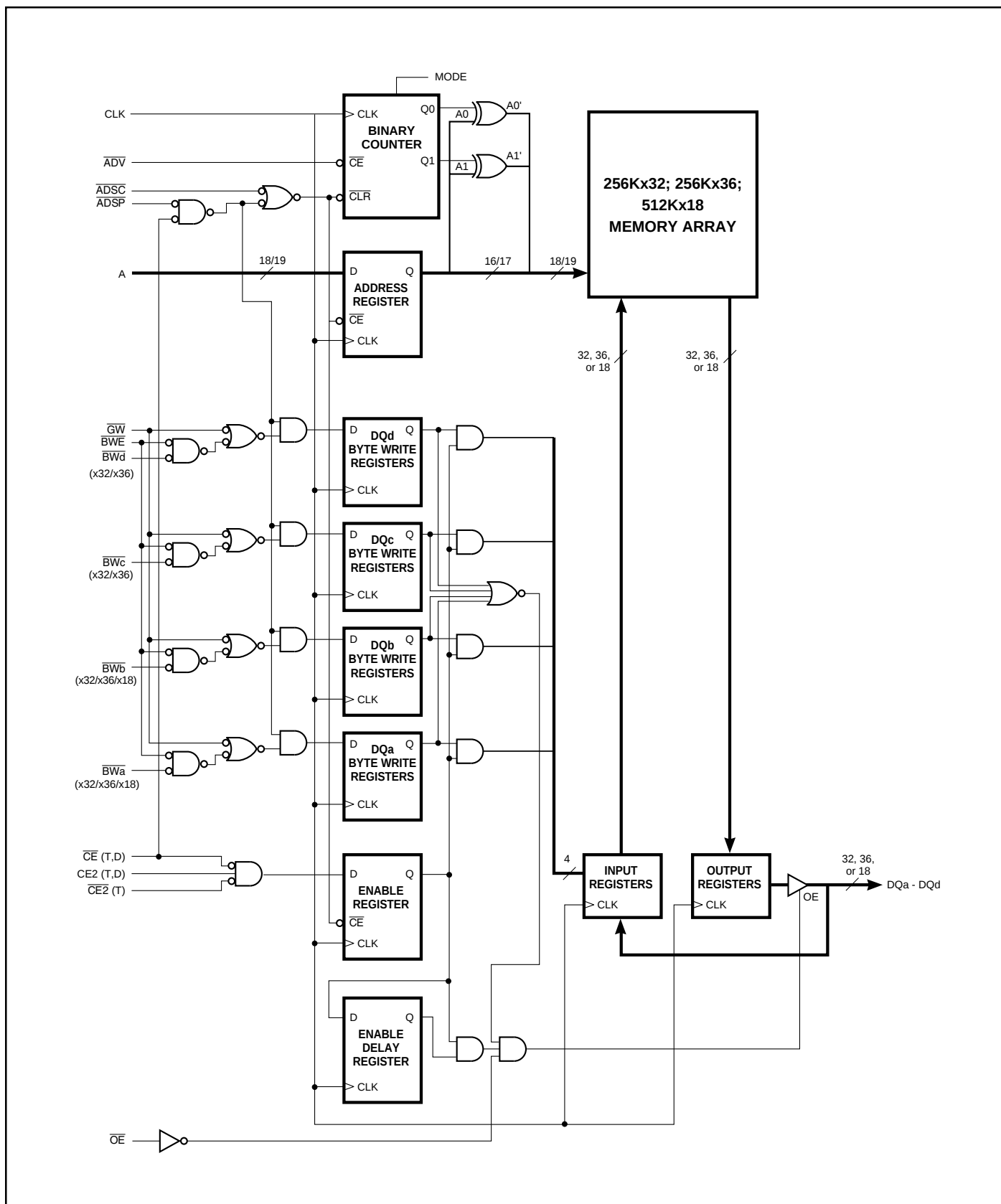
The mode pin is used to select the burst sequence order, Linear burst is achieved when this pin is tied LOW. Interleave burst is achieved when this pin is tied HIGH or left floating.

FAST ACCESS TIME

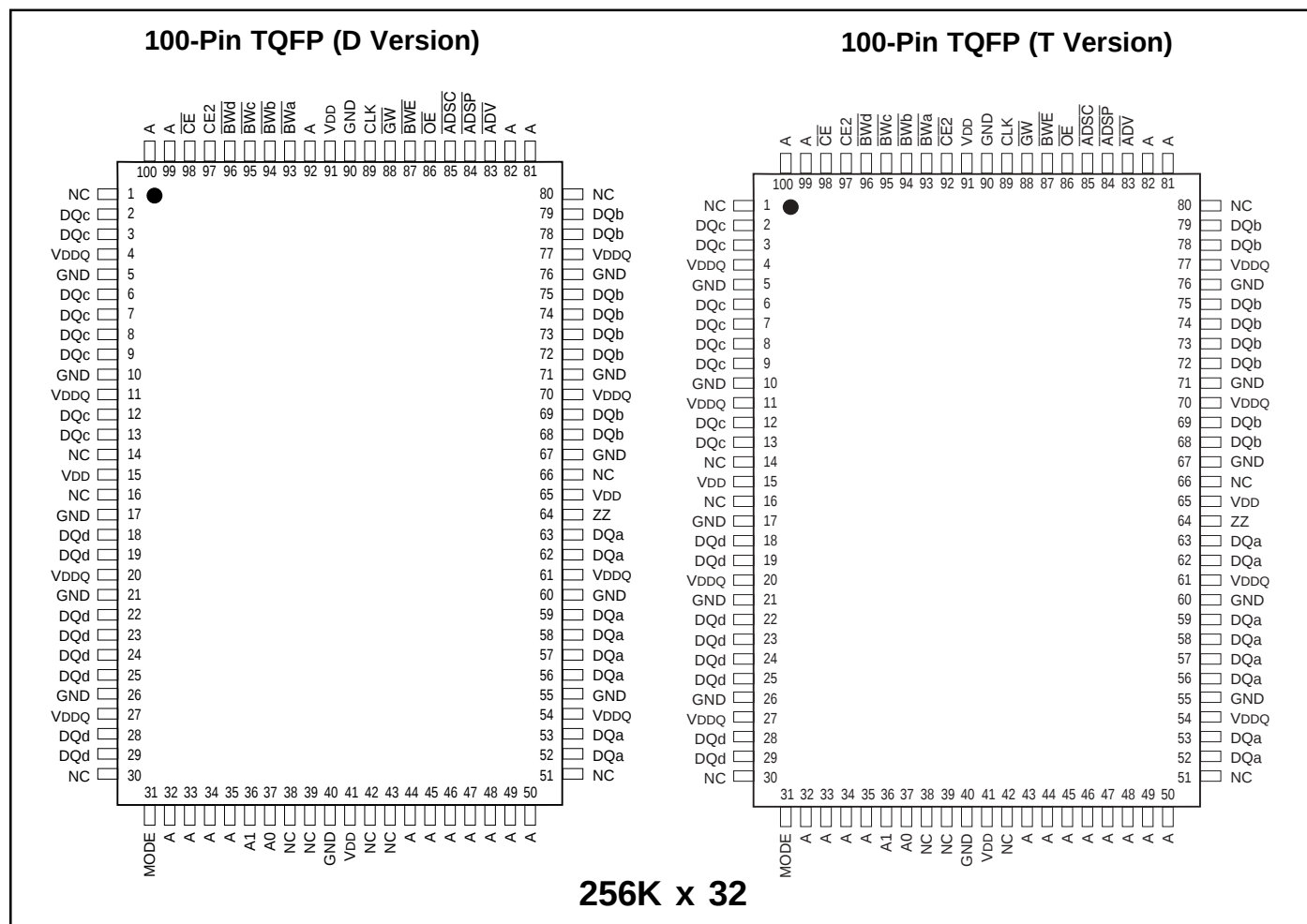
Symbol	Parameter	-200	-166	Units
tkQ	Clock Access Time	3.1	3.5	ns
tkC	Cycle Time	5	6	ns
	Frequency	200	166	MHz

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BLOCK DIAGRAM



PIN CONFIGURATION

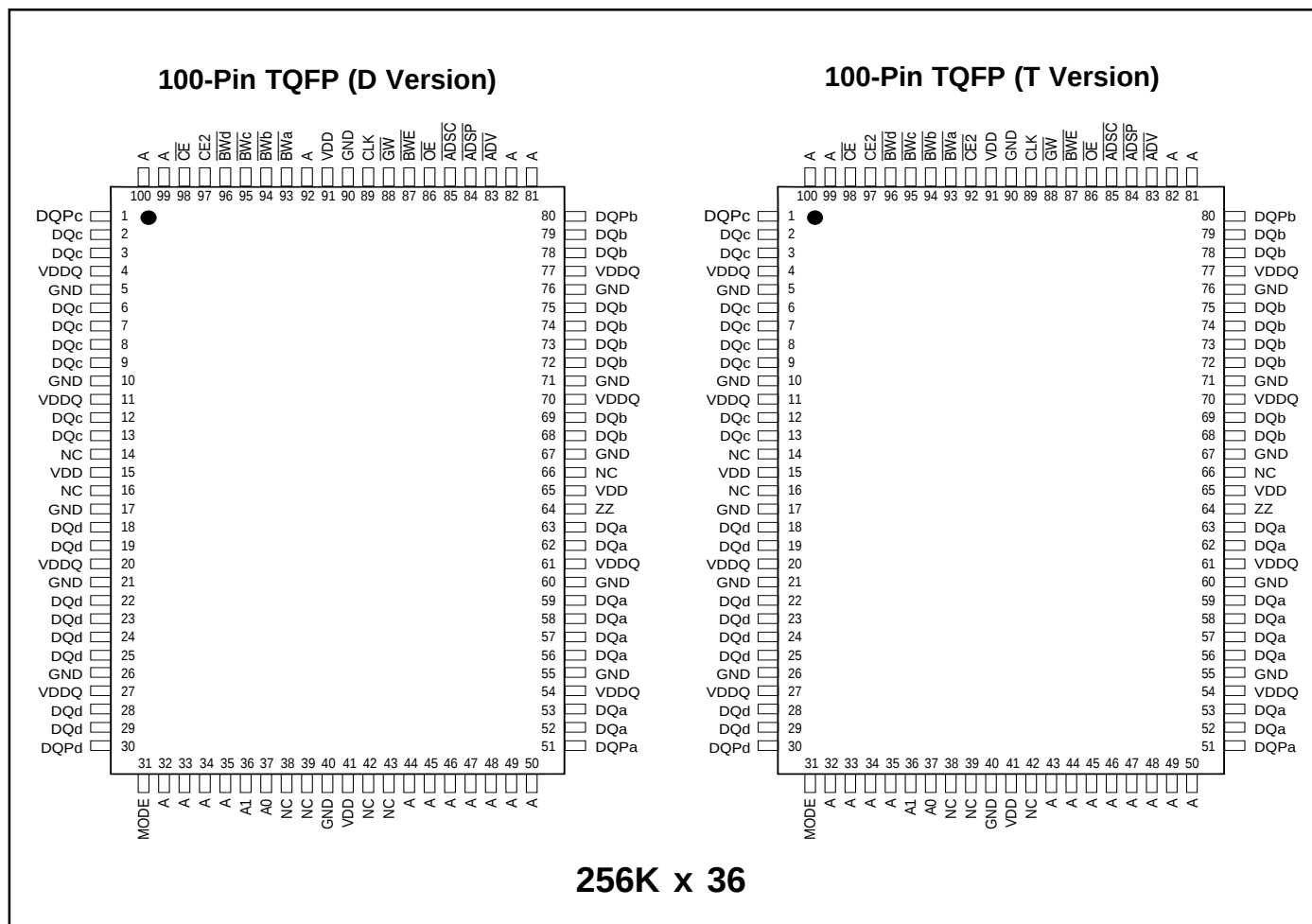


PIN DESCRIPTIONS

A0, A1	Synchronous Address Inputs. These pins must tied to the two LSBs of the address bus.
A	Synchronous Address Inputs
CLK	Synchronous Clock
ADSP	Synchronous Processor Address Status
ADSC	Synchronous Controller Address Status
ADV	Synchronous Burst Address Advance
BWa-BWd	Individual Byte Write Enable
BWE	Synchronous Byte Write Enable

GW	Synchronous Global Write Enable
CE, CE2, CE2	Synchronous Chip Enable
OE	Output Enable
DQa-DQd	Synchronous Data Input/Output
MODE	Burst Sequence Mode Selection
VDD	+3.3V Power Supply
GND	Ground
VDDQ	Isolated Output Buffer Supply: +3.3V or 2.5V
ZZ	Snooze Enable
DQPa-DQPd	Parity Data I/O

PIN CONFIGURATION

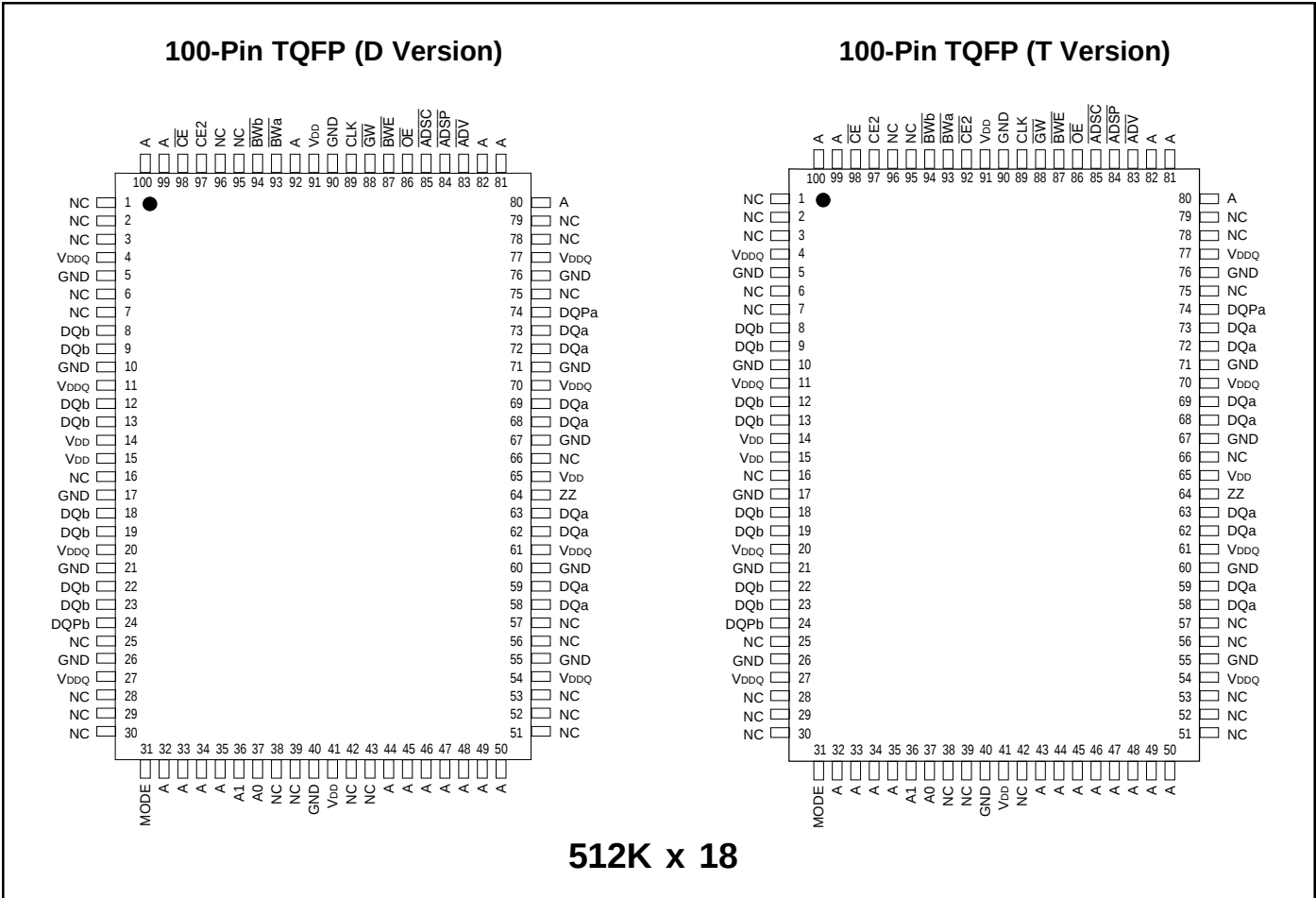


PIN DESCRIPTIONS

A0, A1	Synchronous Address Inputs. These pins must tied to the two LSBs of the address bus.
A	Synchronous Address Inputs
CLK	Synchronous Clock
ADSP	Synchronous Processor Address Status
ADSC	Synchronous Controller Address Status
ADV	Synchronous Burst Address Advance
BW _a -BW _d	Individual Byte Write Enable
BWE	Synchronous Byte Write Enable

$\overline{\text{GW}}$	Synchronous Global Write Enable
$\overline{\text{CE}}$, CE2, CE2	Synchronous Chip Enable
$\overline{\text{OE}}$	Output Enable
DQ _a -DQ _d	Synchronous Data Input/Output
MODE	Burst Sequence Mode Selection
V _{DD}	+3.3V Power Supply
GND	Ground
V _{DDQ}	Isolated Output Buffer Supply: +3.3V or 2.5V
ZZ	Snooze Enable
DQPa-DQPd	Parity Data I/O

PIN CONFIGURATION



PIN DESCRIPTIONS

A0, A1	Synchronous Address Inputs. These pins must tied to the two LSBs of the address bus.	GW	Synchronous Global Write Enable
A	Synchronous Address Inputs	CE, CE2, CE2	Synchronous Chip Enable
CLK	Synchronous Clock	OE	Output Enable
ADSP	Synchronous Processor Address Status	DQa-DQd	Synchronous Data Input/Output
ADSC	Synchronous Controller Address Status	MODE	Burst Sequence Mode Selection
ADV	Synchronous Burst Address Advance	VDD	+3.3V Power Supply
BWa-BWd	Individual Byte Write Enable	GND	Ground
BWE	Synchronous Byte Write Enable	VDDQ	Isolated Output Buffer Supply: +3.3V or 2.5V
		ZZ	Snooze Enable
		DQPa-DQPd	Parity Data I/O

TRUTH TABLE⁽¹⁻⁸⁾

OPERATION	ADDRESS	$\overline{CE}$	$\overline{CE2}$	$CE2$	ZZ	$\overline{ADSP}$	$\overline{ADSC}$	$\overline{ADV}$	WRITE	$\overline{OE}$	CLK	DQ
Deselect Cycle, Power-Down	None	H	X	X	L	X	L	X	X	X	L-H	High-Z
Deselect Cycle, Power-Down	None	L	X	L	L	L	X	X	X	X	L-H	High-Z
Deselect Cycle, Power-Down	None	L	H	X	L	L	X	X	X	X	L-H	High-Z
Deselect Cycle, Power-Down	None	L	X	L	L	H	L	X	X	X	L-H	High-Z
Deselect Cycle, Power-Down	None	L	H	X	L	H	L	X	X	X	L-H	High-Z
Snooze Mode, Power-Down	None	X	X	X	H	X	X	X	X	X	X	High-Z
Read Cycle, Begin Burst	External	L	L	H	L	L	X	X	X	L	L-H	Q
Read Cycle, Begin Burst	External	L	L	H	L	L	X	X	X	H	L-H	High-Z
Write Cycle, Begin Burst	External	L	L	H	L	H	L	X	L	X	L-H	D
Read Cycle, Begin Burst	External	L	L	H	L	H	L	X	H	L	L-H	Q
Read Cycle, Begin Burst	External	L	L	H	L	H	L	X	H	H	L-H	High-Z
Read Cycle, Continue Burst	Next	X	X	X	L	H	H	L	H	L	L-H	Q
Read Cycle, Continue Burst	Next	X	X	X	L	H	H	L	H	H	L-H	High-Z
Read Cycle, Continue Burst	Next	H	X	X	L	X	H	L	H	L	L-H	Q
Read Cycle, Continue Burst	Next	H	X	X	L	X	H	L	H	H	L-H	High-Z
Write Cycle, Continue Burst	Next	X	X	X	L	H	H	L	L	X	L-H	D
Write Cycle, Continue Burst	Next	H	X	X	L	X	H	L	L	X	L-H	D
Read Cycle, Suspend Burst	Current	X	X	X	L	H	H	H	H	L	L-H	Q
Read Cycle, Suspend Burst	Current	X	X	X	L	H	H	H	H	H	L-H	High-Z
Read Cycle, Suspend Burst	Current	H	X	X	L	X	H	H	H	L	L-H	Q
Read Cycle, Suspend Burst	Current	H	X	X	L	X	H	H	H	H	L-H	High-Z
Write Cycle, Suspend Burst	Current	X	X	X	L	H	H	H	L	X	L-H	D
Write Cycle, Suspend Burst	Current	H	X	X	L	X	H	H	L	X	L-H	D

NOTE:

1. X means "Don't Care." H means logic HIGH. L means logic LOW.
2. For WRITE, L means one or more byte write enable signals ($\overline{BWA}$, $\overline{BWb}$, $\overline{BWC}$ or $\overline{BWD}$) and $\overline{BWE}$ are LOW or $\overline{GW}$ is LOW. WRITE = H for all $\overline{BWx}$, $\overline{BWE}$, $\overline{GW}$ HIGH.
3. $\overline{BWA}$ enables WRITES to DQa's and DQPa. $\overline{BWb}$ enables WRITES to DQb's and DQPb. $\overline{BWC}$ enables WRITES to DQc's and DQPC. $\overline{BWD}$ enables WRITES to DQd's and DQPD. DQPa and DQPb are only available on the x18 and x36 versions. DQPC and DQPD are only available on the x36 version.
4. All inputs except $\overline{OE}$ and ZZ must meet setup and hold times around the rising edge (LOW to HIGH) of CLK.
5. Wait states are inserted by suspending burst.
6. For a WRITE operation following a READ operation, $\overline{OE}$ must be HIGH before the input data setup time and held HIGH during the input data hold time.
7. This device contains circuitry that will ensure the outputs will be in High-Z during power-up.
8. $\overline{ADSP}$ LOW always initiates an internal READ at the L-H edge of CLK. A WRITE is performed by setting one or more byte write enable signals and $\overline{BWE}$ LOW or $\overline{GW}$ LOW for the subsequent L-H edge of CLK. See WRITE timing diagram for clarification.

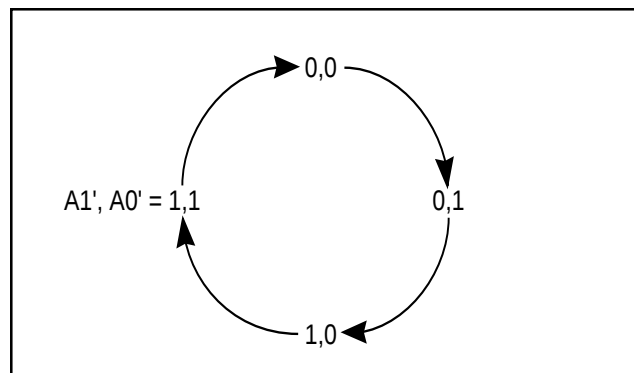
PARTIAL TRUTH TABLE

Function	$\overline{GW}$	$\overline{BWE}$	$\overline{BWA}$	$\overline{BWb}$	$\overline{BWc}$	$\overline{BWd}$
Read	H	H	X	X	X	X
Read	H	L	H	H	H	H
Write Byte 1	H	L	L	H	H	H
Write All Bytes	H	L	L	L	L	L
Write All Bytes	L	X	X	X	X	X

OPERATING RANGE

Range	Ambient Temperature	V _{DD}	V _{DDQ}
Commercial	0°C to +70°C	3.3V ± 5%	3.3V ± 5%
			2.5V ± 5%
Industrial	-40°C to +85°C	3.3V ± 5%	3.3V ± 5%
			2.5V ± 5%

LINEAR BURST ADDRESS TABLE (MODE = GND)

INTERLEAVED BURST ADDRESS TABLE (MODE = V_{DD} or No Connect)

External Address A1 A0	1st Burst Address A1 A0	2nd Burst Address A1 A0	3rd Burst Address A1 A0
00	01	10	11
01	00	11	10
10	11	00	01
11	10	01	00

ABSOLUTE MAXIMUM RATINGS⁽¹⁾

Symbol	Parameter	Value	Unit
T _{STG}	Storage Temperature	–55 to +150	°C
P _D	Power Dissipation	1.6	W
I _{OUT}	Output Current (per I/O)	100	mA
V _{IN} , V _{OUT}	Voltage Relative to GND for I/O Pins	–0.5 to V _{DDQ} + 0.5	V
V _{IN}	Voltage Relative to GND for for Address and Control Inputs	–0.5 to V _{DD} + 0.5	V
V _{DD}	Voltage on V _{DD} Supply Relative to GND	–0.5 to 4.6	V

Notes:

1. Stress greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
2. This device contains circuitry to protect the inputs against damage due to high static voltages or electric fields; however, precautions may be taken to avoid application of any voltage higher than maximum rated voltages to this high-impedance circuit.
3. This device contains circuitry that will ensure the output devices are in High-Z at power up.

DCELECTRICAL CHARACTERISTICS (Over Operating Range)

Symbol	Parameter	Test Conditions	2.5V (I/O)		3.3V (I/O)		Unit
			Min.	Max.	Min.	Max.	
V _{OH}	Output HIGH Voltage	I _{OH} = –4.0 mA (3.3V) I _{OH} = 1.0 mA (2.5V)	2.0	—	2.4	—	V
V _{OL}	Output LOW Voltage	I _{OL} = 8.0 mA (3.3V) I _{OL} = 1.0 mA (2.5V)	—	0.4	—	0.4	V
V _{IH}	Input HIGH Voltage		1.7	V _{DD} + 0.3	2.0	V _{DD} + 0.3	V
V _{IL}	Input LOW Voltage		–0.3	0.7	–0.3	0.8	V
I _{LI}	Input Leakage Current	GND ≤ V _{IN} ≤ V _{DD} ⁽¹⁾	–5	5	–5	5	μA
I _{LO}	Output Leakage Current	GND ≤ V _{OUT} ≤ V _{DDQ} , $\overline{OE} = V_I$	–5	5	–5	5	μA

POWER SUPPLY CHARACTERISTICS⁽¹⁾ (Over Operating Range)

Symbol	Parameter	Test Conditions		-200		-166		Unit
				Max x18	Max x36	Max x18	Max x36/x32	
I _{CC}	AC Operating Supply Current	Device Selected, $\overline{OE} = V_{IH}$, $ZZ \leq V_{IL}$, All Inputs $\leq V_{IL}$ or $\geq V_{IH}$, Cycle Time $\geq t_{KC}$ min.	Com.	125	130	120	125	mA
			Ind.	135	140	130	135	
I _{SB}	Standby Current TTL Input	Device Deselected, $V_{DD} = \text{Max.}$, All Inputs $\leq V_{IL}$ or $\geq V_{IH}$, $ZZ \leq V_{IL}$, $f = \text{Max.}$	Com.	55	55	50	50	mA
			Ind.	60	60	55	55	
I _{SBI}	Standby Current CMOS Input	Device Deselected, $V_{DD} = \text{Max.}$, $V_{IN} \leq \text{GND} + 0.2\text{V}$ or $\geq V_{DD} - 0.2\text{V}$, $f = 0$	Com.	30	30	30	30	mA
			Ind.	40	40	40	40	

Note:

1. MODE pin has an internal pullup and should be tied to V_{DD} or GND. It exhibits $\pm 30 \mu\text{A}$ maximum leakage current when tied to $\leq \text{GND} + 0.2\text{V}$ or $\geq V_{DD} - 0.2\text{V}$.

CAPACITANCE^(1,2)

Symbol	Parameter	Conditions	Max.	Unit
C _{IN}	Input Capacitance	V _{IN} = 0V	6	pF
C _{OUT}	Input/Output Capacitance	V _{OUT} = 0V	8	pF

Notes:

1. Tested initially and after any design or process changes that may affect these parameters.
2. Test conditions: T_A = 25°C, f = 1 MHz, V_{DD} = 3.3V.

3.3V I/O AC TEST CONDITIONS

Parameter	Unit
Input Pulse Level	0V to 3.0V
Input Rise and Fall Times	1ns
Input and Output Timing and Reference Level	1.5V
Output Load	See Figures 1 and 2

3.3V I/O OUTPUT LOAD EQUIVALENT

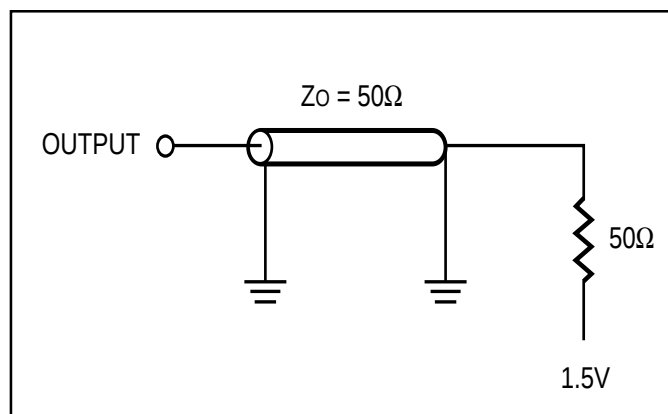


Figure 1

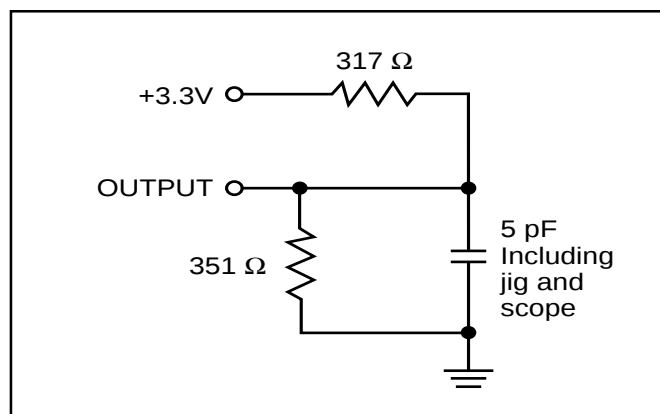


Figure 2

2.5V I/O AC TEST CONDITIONS

Parameter	Unit
Input Pulse Level	0V to 2.5V
Input Rise and Fall Times	1 ns
Input and Output Timing and Reference Level	1.25V
Output Load	See Figures 3 and 4

2.5V I/O OUTPUT LOAD EQUIVALENT

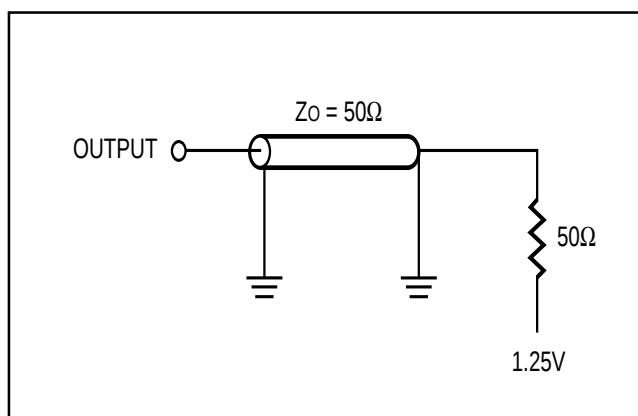


Figure 3

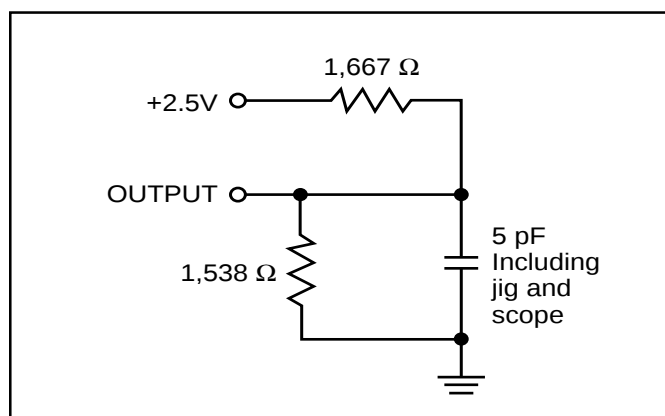


Figure 4

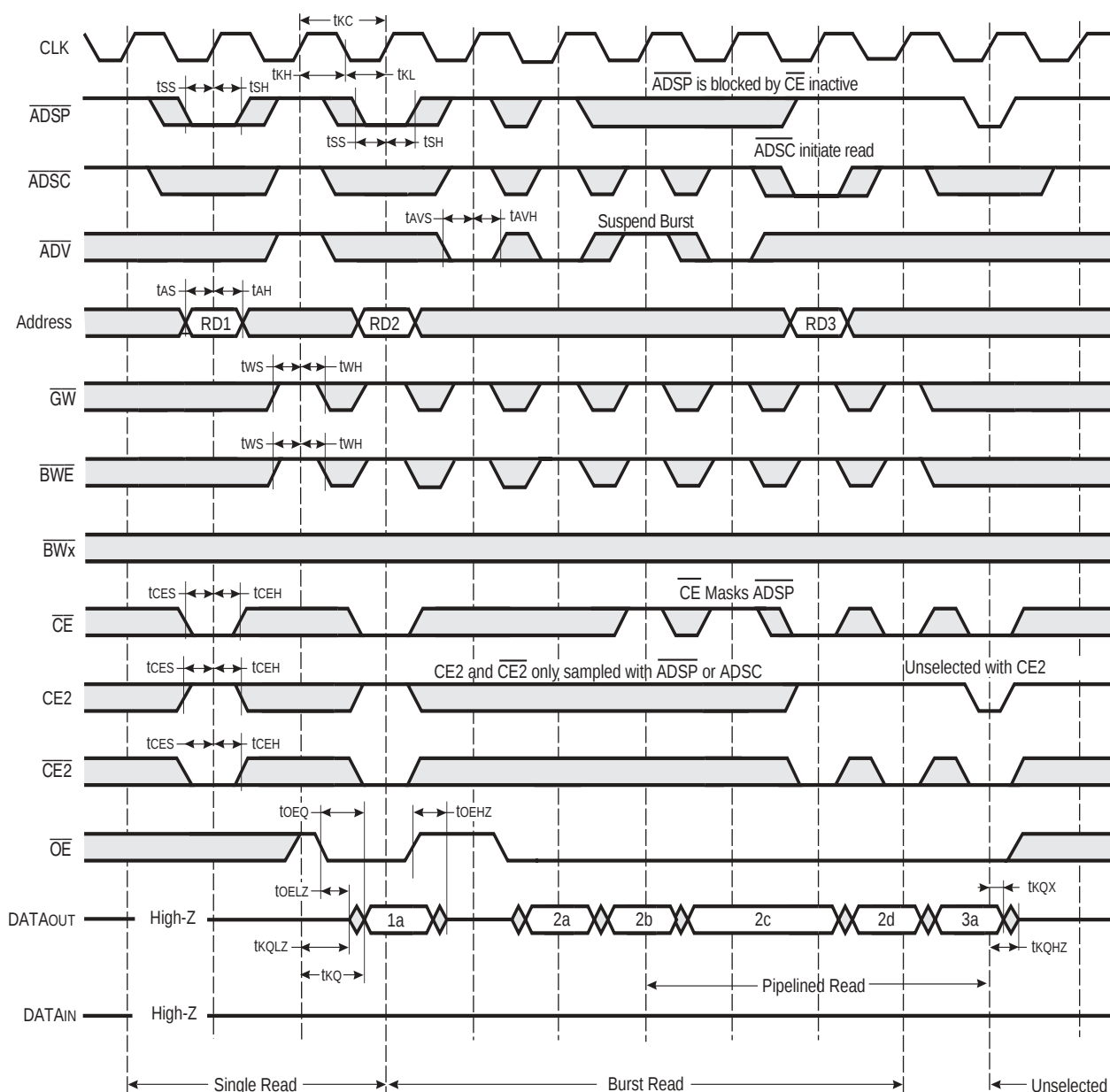
Read/WRITE CYCLE SWITCHING CHARACTERISTICS (Over Operating Range)

Symbol	Parameter	-166		-200		Unit
		Min.	Max.	Min.	Max.	
f _{MAX}	Clock Frequency	—	166	—	200	ns
t _{KC}	Cycle Time	6	—	5	—	ns
t _{KH}	Clock High Pulse Width	2.3	—	2	—	ns
t _{KL}	Clock Low Pulse Width	2.3	—	2	—	ns
t _{KQ}	Clock Access Time	—	3.5	—	3.1	ns
t _{KQX} ⁽¹⁾	Clock High to Output Invalid	1.5	—	1.0	—	ns
t _{KQLZ} ^(1,2)	Clock High to Output Low-Z	0	—	0	—	ns
t _{KQHZ} ^(1,2)	Clock High to Output High-Z	—	3.5	—	3.0	ns
t _{OEQ}	Output Enable to Output Valid	—	3.5	—	3.1	ns
t _{OELZ} ^(1,2)	Output Enable to Output Low-Z	0	—	0	—	ns
t _{OEZH} ^(1,2)	Output Enable to Output High-Z	—	3.5	—	3.0	ns
t _{AS}	Address Setup Time	1.5	—	1.4	—	ns
t _{SS}	Address Status Setup Time	1.5	—	1.4	—	ns
t _{WS}	Write Setup Time	1.5	—	1.4	—	ns
t _{CES}	Chip Enable Setup Time	1.5	—	1.4	—	ns
t _{AVS}	Address Advance Setup Time	1.5	—	1.4	—	ns
t _{AH}	Address Hold Time	0.5	—	0.4	—	ns
t _{SH}	Address Status Hold Time	0.5	—	0.4	—	ns
t _{WH}	Write Hold Time	0.5	—	0.4	—	ns
t _{CEH}	Chip Enable Hold Time	0.5	—	0.4	—	ns
t _{AVH}	Address Advance Hold Time	0.5	—	0.4	—	ns

Note:

1. Guaranteed but not 100% tested. This parameter is periodically sampled.
2. Tested with load in Figure 1,2,3,4.

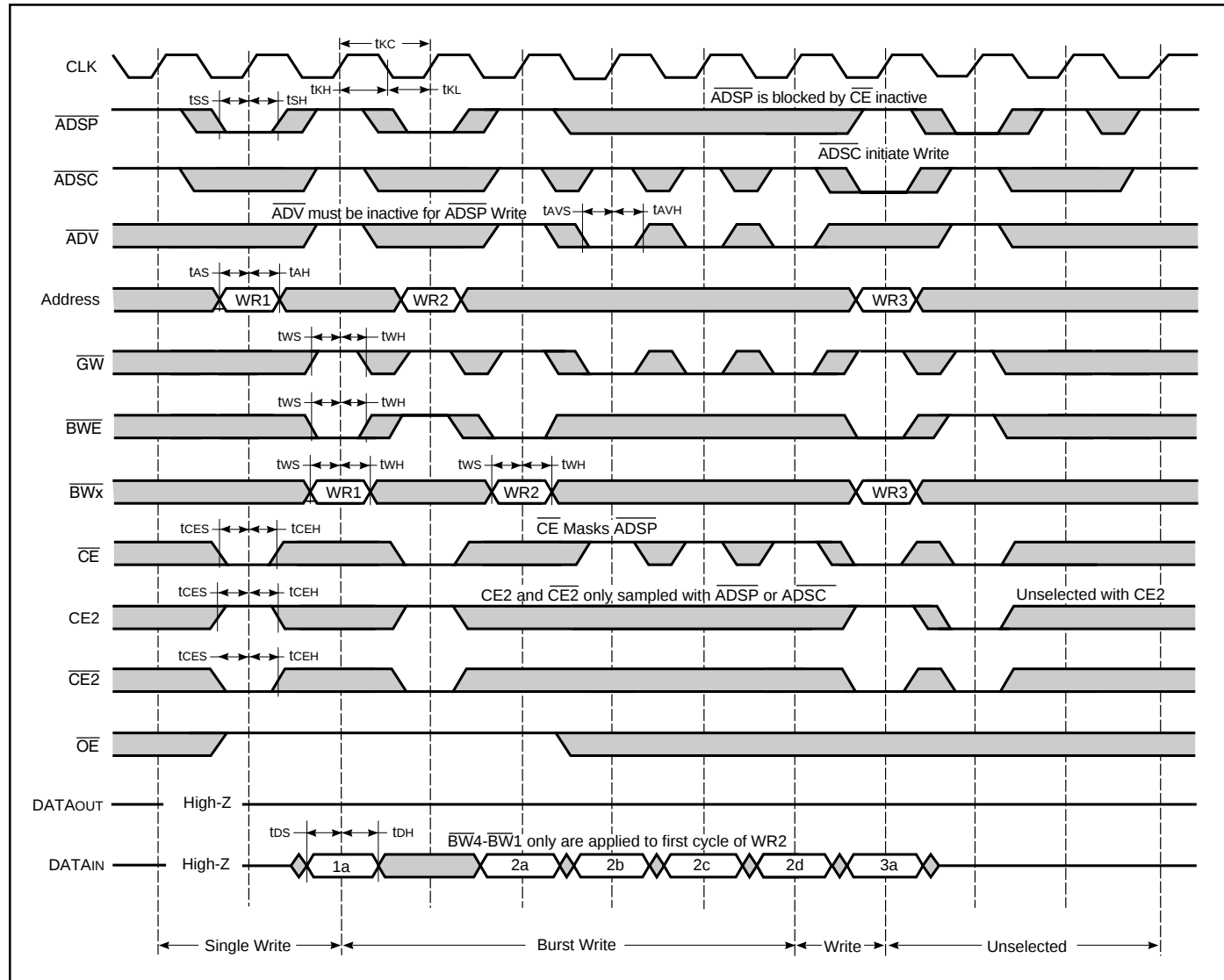
READ/WRITE CYCLE TIMING



WRITE CYCLE SWITCHING CHARACTERISTICS (Over Operating Range)

Symbol	Parameter	-166		-200		Unit
		Min.	Max.	Min.	Max.	
t _{CC}	Cycle Time	6	—	5	—	ns
t _{KH}	Clock High Pulse Width	2.3	—	2	—	ns
t _{KL}	Clock Low Pulse Width	2.3	—	2	—	ns
t _{AS}	Address Setup Time	1.5	—	1.4	—	ns
t _{SS}	Address Status Setup Time	1.5	—	1.4	—	ns
t _{WS}	Write Setup Time	1.5	—	1.4	—	ns
t _{DS}	Data In Setup Time	1.5	—	1.4	—	ns
t _{CES}	Chip Enable Setup Time	1.5	—	1.4	—	ns
t _{AVS}	Address Advance Setup Time	1.5	—	1.4	—	ns
t _{AH}	Address Hold Time	0.5	—	0.4	—	ns
t _{SH}	Address Status Hold Time	0.5	—	0.4	—	ns
t _{DH}	Data In Hold Time	0.5	—	0.4	—	ns
t _{WH}	Write Hold Time	0.5	—	0.4	—	ns
t _{CEH}	Chip Enable Hold Time	0.5	—	0.4	—	ns
t _{AVH}	Address Advance Hold Time	0.5	—	0.4	—	ns

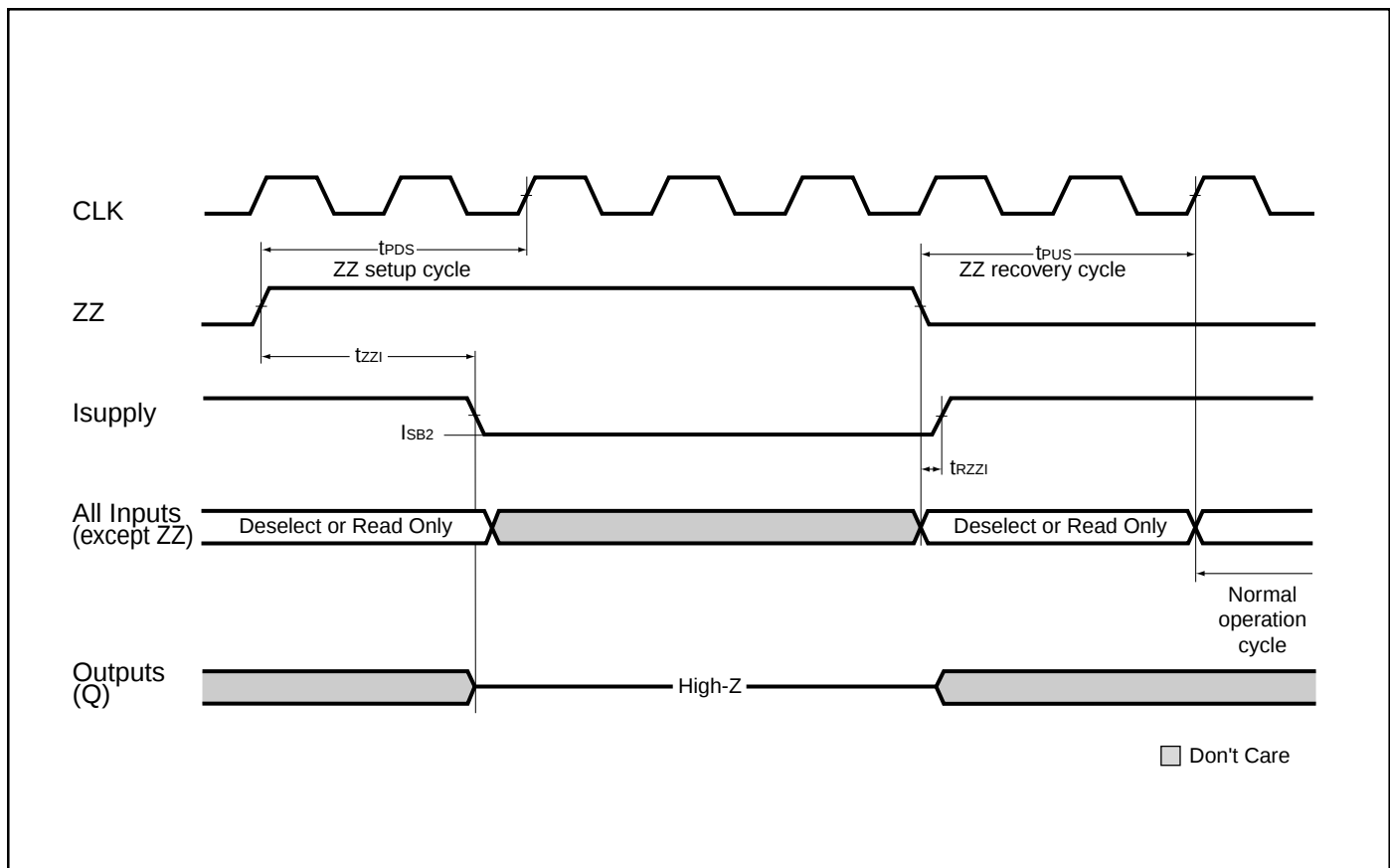
WRITE CYCLE TIMING



SNOOZE MODE ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Conditions	Min.	Max.	Unit
ISB2	Current during SNOOZE MODE	$ZZ \geq V_{ih}$, Com.	—	30	mA
		$ZZ \geq V_{ih}$, Ind.	—	40	
tPUS	ZZ inactive to input sampled		2	—	cycle
tZZI	ZZ active to SNOOZE current		—	2	cycle
trZZI	ZZ inactive to exit SNOOZE current		0	—	ns

SNOOZE MODE TIMING



ORDERING INFORMATION: IS61LPS25632

(T Version)

Commercial Range: 0°C to +70°C

Speed	Order Part Number	Package
166Mhz	IS61LPS25632T-166TQ	TQFP

(D Version)

Commercial Range: 0°C to +70°C

Speed	Order Part Number	Package
166Mhz	IS61LPS25632D-166TQ	TQFP

(T Version)

Industrial Range: -40°C to +85°C

Speed	Order Part Number	Package
166Mhz	IS61LPS25632T-166TQI	TQFP

ORDERING INFORMATION: IS61LPS25636

(T Version)

Commercial Range: 0°C to +70°C

Speed	Order Part Number	Package
166Mhz	IS61LPS25636T-166TQ	TQFP

(T Version)

Industrial Range: -40°C to +85°C

Speed	Order Part Number	Package
166Mhz	IS61LPS25636T-166TQI	TQFP
200Mhz	IS61LPS25636T-200TQI	TQFP

(D Version)

Commercial Range: 0°C to +70°C

Speed	Order Part Number	Package
166Mhz	IS61LPS25636D-166TQ	TQFP

(D Version)

Industrial Range: -40°C to +85°C

Speed	Order Part Number	Package
166Mhz	IS61LPS25636D-166TQI	TQFP

ORDERING INFORMATION: IS61LPS51218

(T Version)

Commercial Range: 0°C to +70°C

Speed	Order Part Number	Package
166Mhz	IS61LPS51218T-166TQ	TQFP

(T Version)

Industrial Range: -40°C to +85°C

Speed	Order Part Number	Package
166Mhz	IS61LPS51218T-166TQI	TQFP

(D Version)

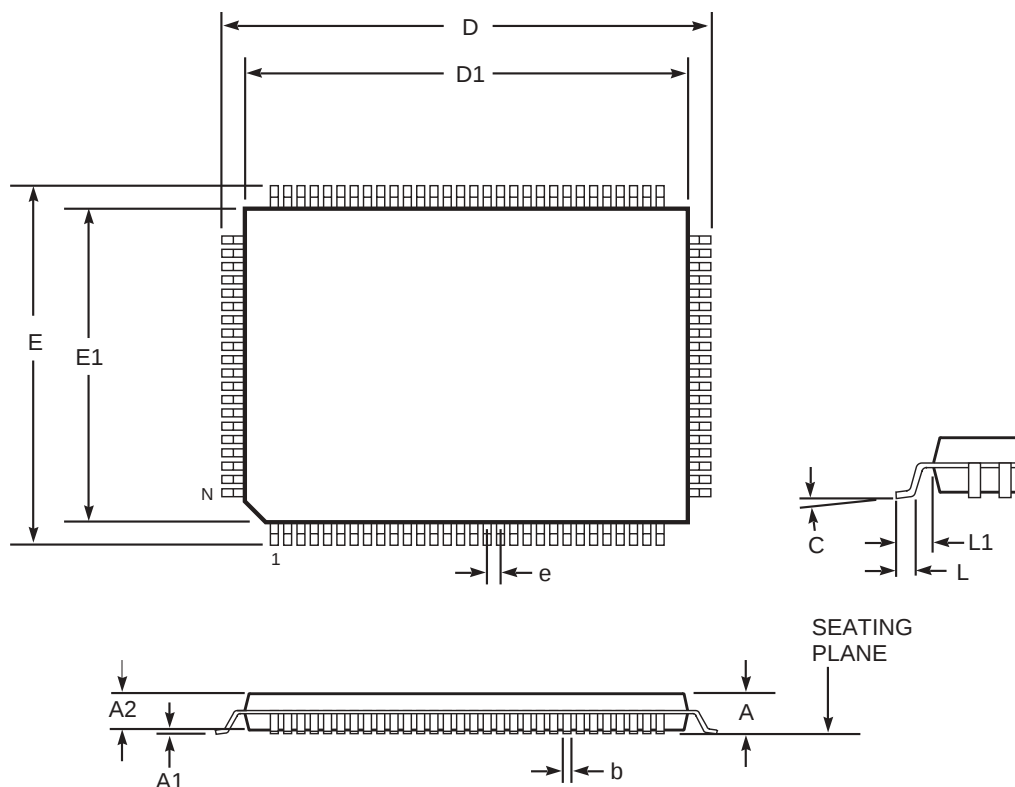
Commercial Range: 0°C to +70°C

Speed	Order Part Number	Package
166Mhz	IS61LPS51218D-166TQ	TQFP

PACKAGING INFORMATION

TQFP (Thin Quad Flat Pack Package)

Package Code: TQ



Thin Quad Flat Pack (TQ)								
Symbol	Millimeters		Inches				Inches	
	Min	Max	Min	Max			Min	Max
Ref. Std.								
No. Leads (N)					100			
					128			
A	—	1.60	—	0.063	—	1.60	—	0.063
A1	0.05	0.15	0.002	0.006	0.05	0.15	0.002	0.006
A2	1.35	1.45	0.053	0.057	1.35	1.45	0.053	0.057
b	0.22	0.38	0.009	0.015	0.17	0.27	0.007	0.011
D	21.90	22.10	0.862	0.870	21.80	22.20	0.858	0.874
D1	19.90	20.10	0.783	0.791	19.90	20.10	0.783	0.791
E	15.90	16.10	0.626	0.634	15.80	16.20	0.622	0.638
E1	13.90	14.10	0.547	0.555	13.90	14.10	0.547	0.555
e	0.65 BSC		0.026 BSC		0.50 BSC		0.020 BSC	
L	0.45	0.75	0.018	0.030	0.45	0.75	0.018	0.030
L1	1.00 REF.		0.039 REF.		1.00 REF.		0.039 REF.	
C	0°	7°	0°	7°	0°	7°	0°	7°

Notes:

1. All dimensioning and tolerancing conforms to ANSI Y14.5M-1982.
2. Dimensions D1 and E1 do not include mold protrusions. Allowable protrusion is 0.25 mm per side. D1 and E1 do include mold mismatch and are determined at datum plane -H-.
3. Controlling dimension: millimeters.